

Isc N-Channel MOSFET Transistor

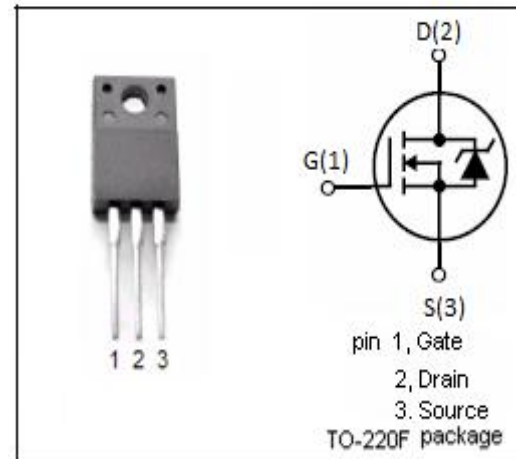
SPA02N80C3

• FEATURES

- With TO-220F package
- Low input capacitance and gate charge
- Reduced switching and conduction losses
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

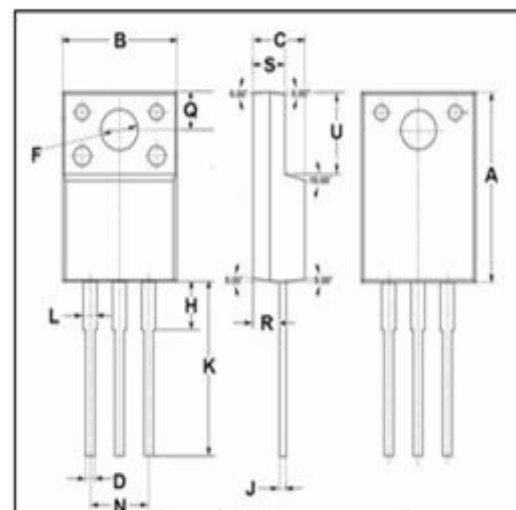
• APPLICATIONS

- Switching applications



• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	800	V
V _{GSS}	Gate-Source Voltage	±30	V
I _D	Drain Current-Continuous @T _c =25°C (V _{GS} at 10V) T _c =100°C	2 1.2	A
I _{DM}	Drain Current-Single Pulsed	6	A
P _D	Total Dissipation @T _c =25°C	30.5	W
T _j	Max. Operating Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55~150	°C



DIM	mm	
	MIN	MAX
A	14.95	15.05
B	10.00	10.10
C	4.40	4.60
D	0.75	0.90
F	3.10	3.30
H	3.70	3.90
J	0.50	0.70
K	13.4	13.6
L	1.10	1.30
N	5.00	5.20
Q	2.70	2.90
R	2.20	2.40
S	2.65	2.90
U	6.40	6.60

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th(ch-c)}	Channel-to-case thermal resistance	4.1	°C/W
R _{th(ch-a)}	Channel-to-ambient thermal resistance	80	°C/W

Isc N-Channel MOSFET Transistor**SPA02N80C3****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V; I_D=0.25mA$	800			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}; I_D=0.12mA$	2.1		3.9	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V; I_D=1.2A$		2400	2700	$m\Omega$
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V; V_{DS}=0V$			± 0.1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=800V; V_{GS}=0V; T_j=25^{\circ}\text{C}$ $V_{DS}=800V; V_{GS}=0V; T_j=150^{\circ}\text{C}$			1 100	μA
V_{SDF}	Diode forward voltage	$I_{SD}=2A, V_{GS}=0V$		1.0	1.2	V

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